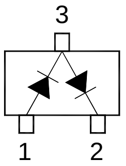
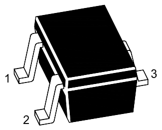
1SS372W

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- High speed switching





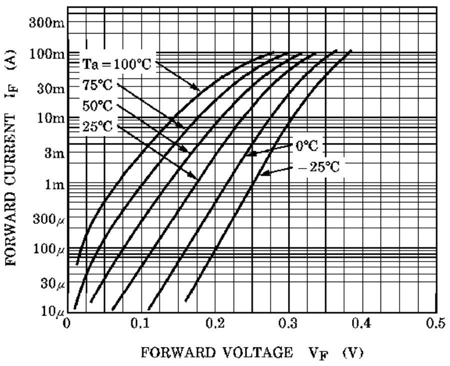
SOT-323 Plastic Package
Marking Code: ME

Absolute Maximum Ratings (T_a = 25 °C)

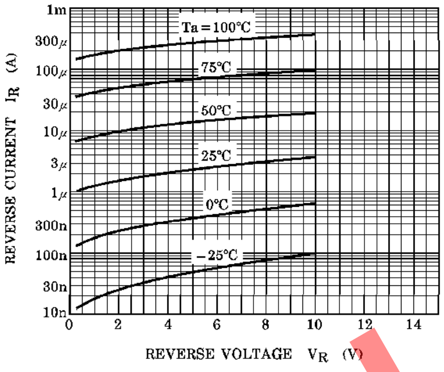
Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Average Forward Current	I_O	100	mA
Maximum Peak Forward Current	I_{FM}	200	mA
Peak Forward Surge Current (t_p = 10 ms)	I_{FSM}	1	A
Power Dissipation	P_d	100	mW
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

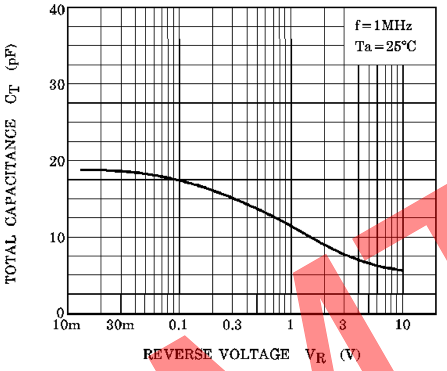
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 5 mA at I_F = 100 mA	V_F	0.3 0.5	V
Reverse Current at V_R = 10 V	I_R	20	µA
Total Capacitance at V_R = 0, f = 1 MHz	C_T	40	pF



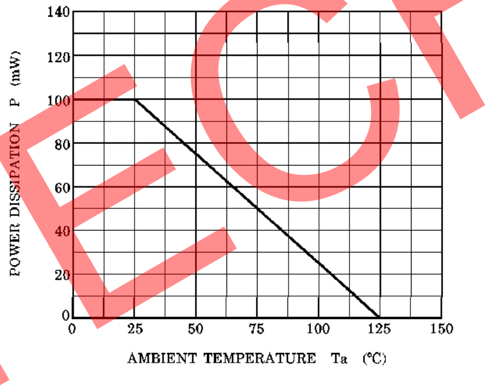
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



P − Ta